

Product Summary

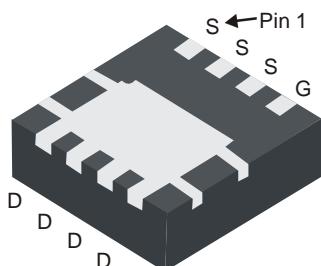
$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_c = +25^\circ C$
60V	7.5mΩ @ $V_{GS} = 10V$	30A
	11.5mΩ @ $V_{GS} = 4.5V$	25A

Description

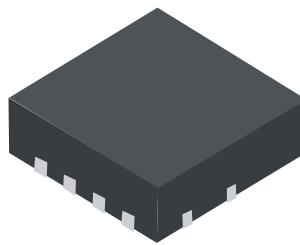
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

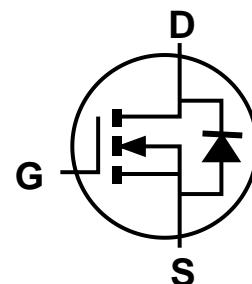
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters



Bottom View



Top View



Equivalent Circuit

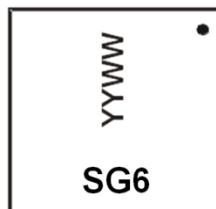
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6010LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT6010LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



SG6 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 13 = 2013)
 WW = Week Code (01 ~ 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	$T_A = +25^\circ\text{C}$	I_D	13
	$T_A = +70^\circ\text{C}$		11
Avalanche Current, $L=0.1\text{mH}$	$T_C = +25^\circ\text{C}$	I_D	30
	$T_C = +70^\circ\text{C}$		24
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	3	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	80	A
Avalanche Current, $L=0.1\text{mH}$	I_{AS}	20	A
Avalanche Energy, $L=0.1\text{mH}$	E_{AS}	20	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	2.2	W
		41	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	55	$^\circ\text{C/W}$
		35	
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	3	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	—	2	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6	7.5	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	7.8	11.5		$V_{GS} = 4.5\text{V}, I_D = 20\text{A}$
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	$V_{GS} = 0\text{V}, I_S = 20\text{A}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{ISS}	—	2,090	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{OSS}	—	746	—		
Reverse Transfer Capacitance	C_{RSS}	—	38.5	—		
Gate resistance	R_G	—	0.59	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_G	—	19.3	—	nC	$V_{DS} = 30\text{V}, I_D = 20\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_G	—	41.3	—		
Gate-Source Charge	Q_{GS}	—	6.0	—		
Gate-Drain Charge	Q_{GD}	—	8.8	—	nS	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, I_D = 20\text{A}, R_G = 3\Omega$
Turn-On Delay Time	$t_{D(ON)}$	—	5.7	—		
Turn-On Rise Time	t_R	—	4.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	23.4	—		
Turn-Off Fall Time	t_F	—	9.7	—		

Notes: 5. $R_{\theta JA}$ is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.

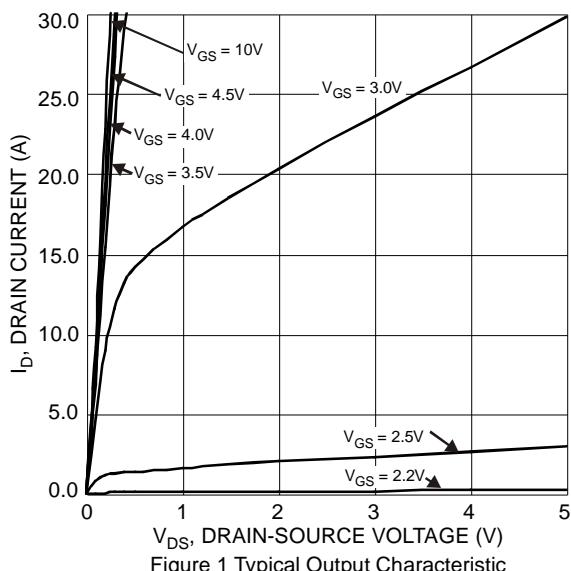


Figure 1 Typical Output Characteristic

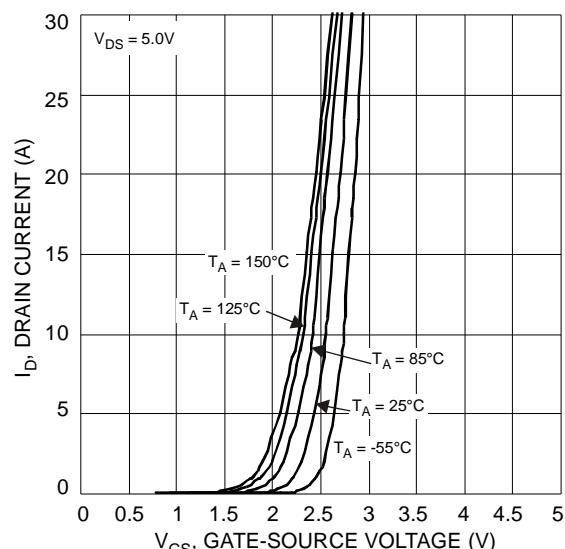


Figure 2 Typical Transfer Characteristics

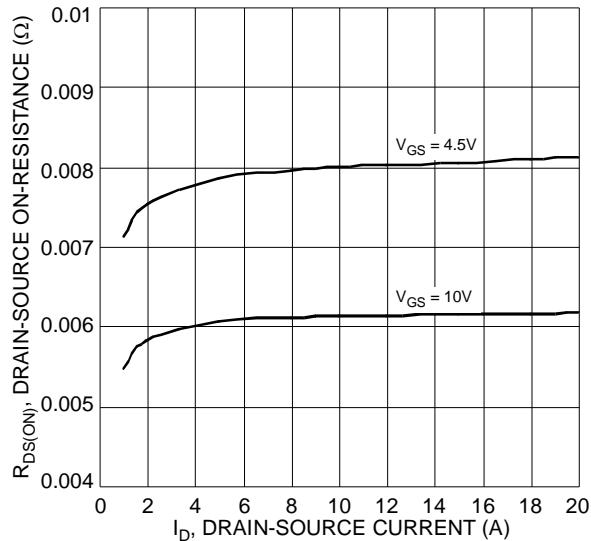


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

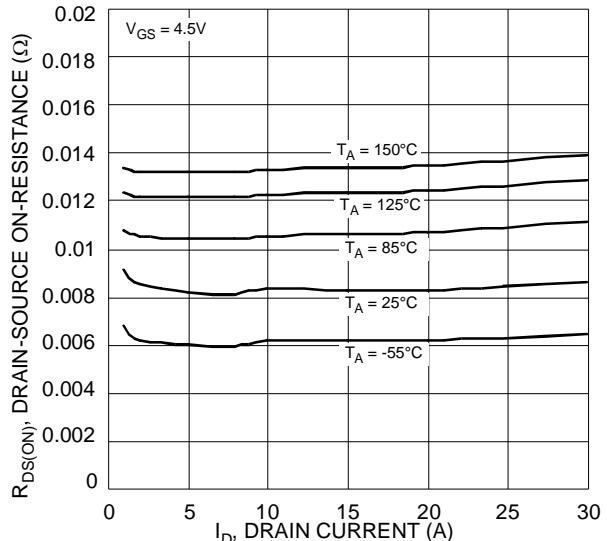


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

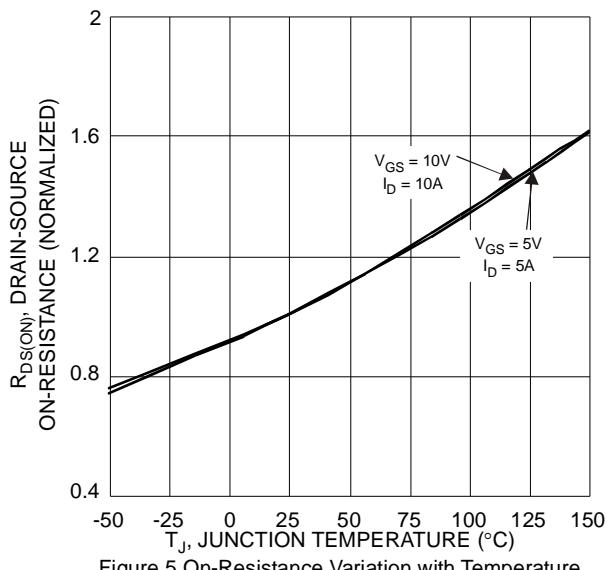


Figure 5 On-Resistance Variation with Temperature

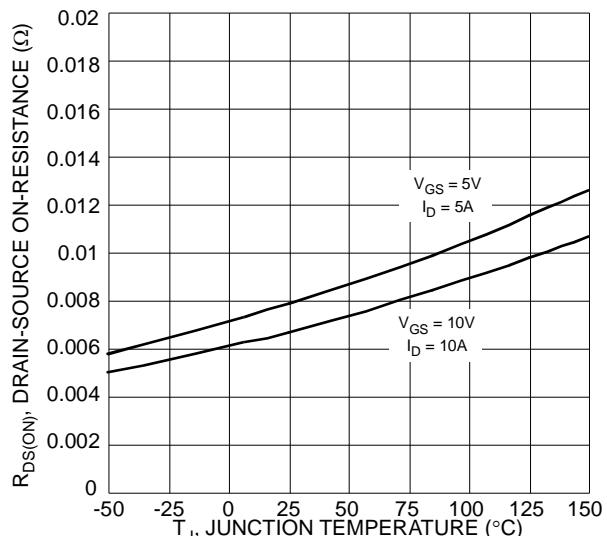


Figure 6 On-Resistance Variation with Temperature

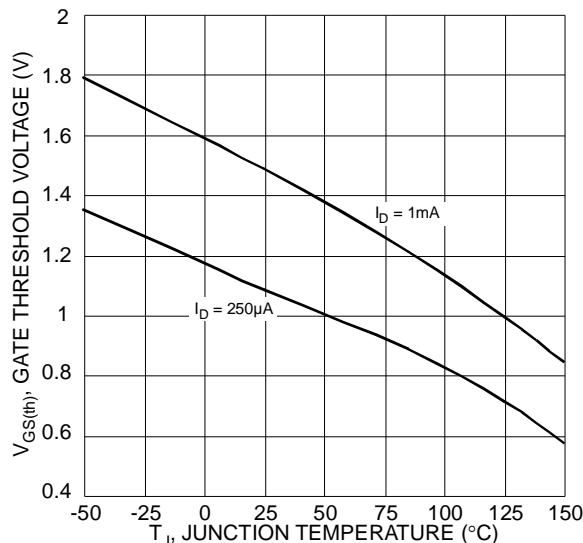


Figure 7 Gate Threshold Variation vs. Ambient Temperature

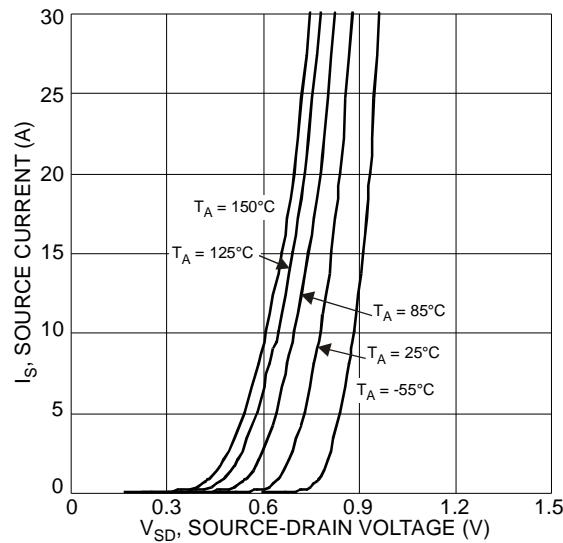


Figure 8 Diode Forward Voltage vs. Current

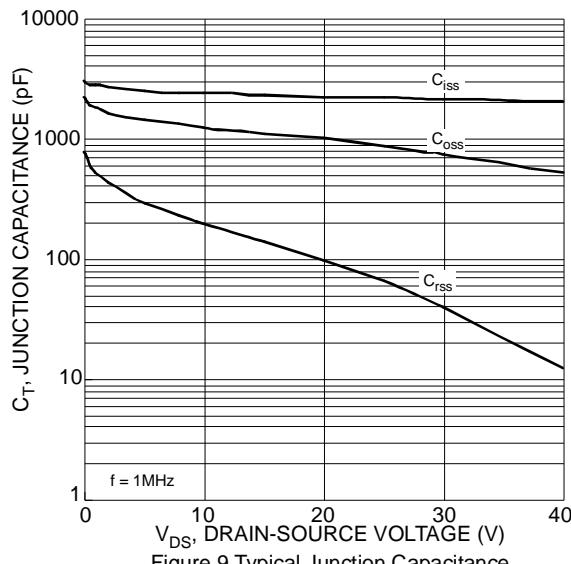


Figure 9 Typical Junction Capacitance

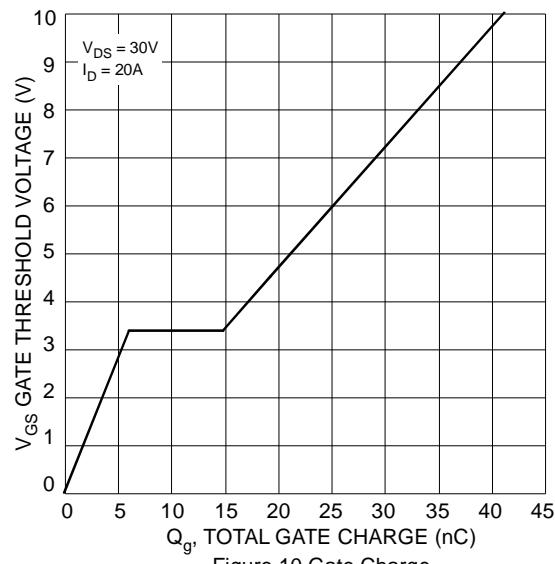


Figure 10 Gate Charge

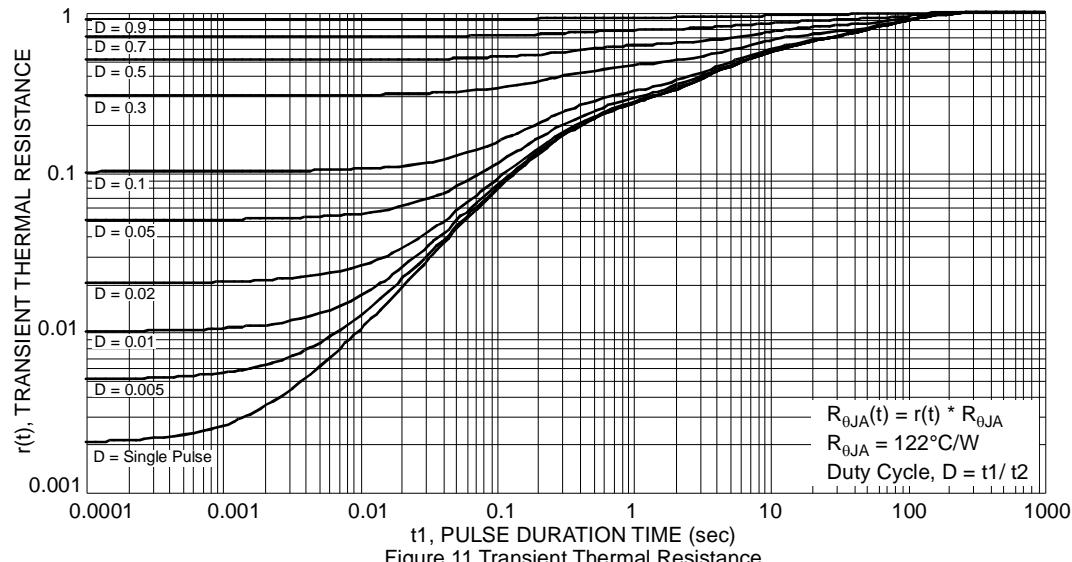
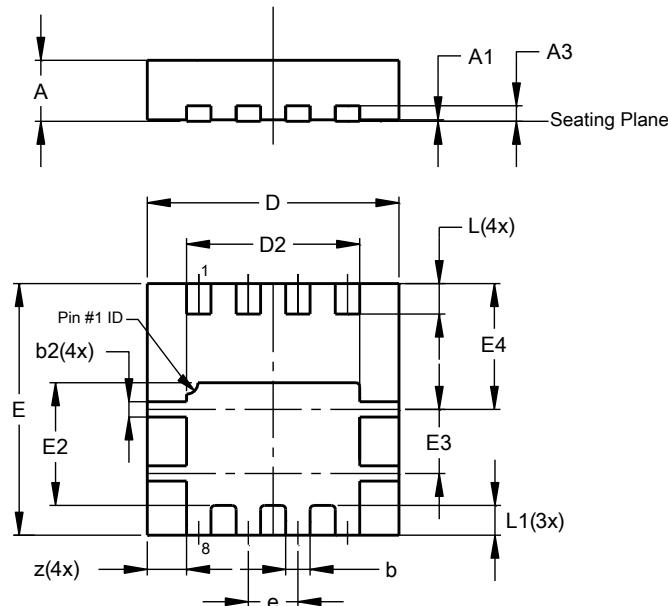


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

PowerDI3333-8



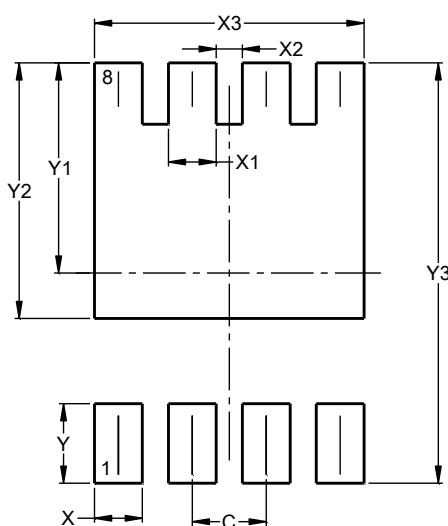
POWERDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	—	—	0.65
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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